

L Number	Hits	Search Text	DB	Time stamp
-	83	(("screen oxide") WITH (implant or implanting)) SAME (remove or removing or removal or removed)	USPAT; US-PGPUB	2002/08/09 16:19
-	9	((("screen oxide") WITH (implant or implanting)) SAME (remove or removing or removal or removed)) SAME trench	USPAT; US-PGPUB	2002/08/09 16:15
-	149	(("sacrificial oxide") WITH (implant or implanting)) SAME (remove or removing or removal or removed)	USPAT; US-PGPUB	2002/08/09 16:22
-	9	((("sacrificial oxide") WITH (implant or implanting) with thermal) SAME (remove or removing or removal or removed))	USPAT; US-PGPUB	2002/08/09 16:24
-	11	((sacrificial) WITH (implant or implanting) with thermal) SAME (remove or removing or removal or removed)	USPAT; US-PGPUB	2002/08/09 16:27
-	11	((sacrificial) WITH (implant or implanting) with thermal) SAME (etch or etching)	USPAT; US-PGPUB	2002/08/09 16:30
-	158	((oxide) WITH (implant or implanting) with thermal) SAME (etch or etching)	USPAT; US-PGPUB	2002/08/09 16:30
-	25	((oxide) WITH (implant or implanting) with thermal) SAME (etch or etching)) same trench	USPAT; US-PGPUB	2002/08/09 17:04
-	1	("6352936").PN.	USPAT; US-PGPUB	2002/08/09 17:07
-	1	("5989963").PN.	USPAT; US-PGPUB	2002/08/09 17:08
-	1	("5976956").PN.	USPAT; US-PGPUB	2002/08/09 17:09
-	0	((("screen oxide" with through with (thermal or thermally)) and (semiconductor or "integrated circuit")) NOT (@ad>06002001 or @rlad>06002001))	USPAT; US-PGPUB	2002/08/09 17:16
-	0	((("screen oxide" with through) SAME (thermal or thermally)) and (semiconductor or "integrated circuit")) NOT (@ad>06002001 or @rlad>06002001))	USPAT; US-PGPUB	2002/08/09 17:15
-	0	((("screen oxide" with through) and (thermal or thermally)) and (semiconductor or "integrated circuit")) NOT (@ad>06002001 or @rlad>06002001))	USPAT; US-PGPUB	2002/08/09 17:14
-	0	((("screen oxide" with (thermal or thermally)) and (semiconductor or "integrated circuit")) NOT (@ad>06002001 or @rlad>06002001))	USPAT; US-PGPUB	2002/08/09 17:14
-	0	((("screen oxide" same (thermal or thermally)) and (semiconductor or "integrated circuit")) NOT (@ad>06002001 or @rlad>06002001))	USPAT; US-PGPUB	2002/08/09 17:15
-	0	((("screen oxide" with through) and (semiconductor or "integrated circuit")) NOT (@ad>06002001 or @rlad>06002001))	USPAT; US-PGPUB	2002/08/09 17:16
-	0	((("screen oxide" with through) and (semiconductor or "integrated circuit")) NOT (@ad>06012001 or @rlad>06012001))	USPAT; US-PGPUB	2002/08/09 17:16
-	108	((("screen oxide" with through) and (semiconductor or "integrated circuit")) NOT (@ad>06012001 or @rlad>06012001))	USPAT; US-PGPUB	2002/08/09 17:16
-	3	((("screen oxide" with through with (thermal or thermally)) and (semiconductor or "integrated circuit"))	USPAT; US-PGPUB	2002/08/09 17:42
-	1	("6265283").PN.	USPAT; US-PGPUB	2002/08/09 17:43

L Number	Hits	Search Text	DB	Time stamp
-	102	("semi recessed" or semirecessed) WITH LOCOS	USPAT; US-PGPUB	2002/08/09 13:59
-	39	((semi recessed" or semirecessed) WITH LOCOS) and ((groove or trench or hole or opening) same (thermal or thermally))	USPAT; US-PGPUB	2002/08/09 14:01
-	29	((("semi recessed" or semirecessed) WITH LOCOS) and ((groove or trench or hole or opening) same (thermal or thermally))) and (ion or implant)	USPAT; US-PGPUB	2002/08/09 14:04
-	23	SROX	USPAT; US-PGPUB	2002/08/09 15:05
-	20	("4135955" "4144101" "4244752" "4280272" "4282648" "4358340" "4385947" "4391849" "4411058" "4412375" "4419142" "4459740" "4468852" "4470191" "4473435" "4480375" "4481705" "4484979" "4509991" "4533431").PN.	USPAT	2002/08/09 14:06
-	8	4600445.URPN.	USPAT	2002/08/09 14:06
-	11	4692992.URPN.	USPAT	2002/08/09 14:09
-	77	((sacrificial) WITH (implant\$)) SAME ((remove or removing or removal or removed or etch or etching) and (trench or recess))	USPAT; US-PGPUB	2002/08/09 15:07

L Number	Hits	Search Text	DB	Time stamp
-	82	"semi recessed" WITH LOCOS	USPAT; US-PGPUB	2002/08/06 10:40
-	52	LOCOS with offset	USPAT; US-PGPUB	2002/08/06 10:54
-	3373	(source or drain) WITH (locos or "field oxide")	USPAT; US-PGPUB	2002/08/06 13:09
-	358	((source or drain) WITH (locos or "field oxide")) and offset	USPAT; US-PGPUB	2002/08/06 11:39
-	2	("4080719" "4102733").PN.	USPAT	2002/08/06 11:02
-	241	438/298.ccls.	USPAT; US-PGPUB	2002/08/06 13:30
-	41	3755001.URPN.	USPAT	2002/08/06 11:44
-	6	("3328216" "3655457" "3755001" "3764396" "3793088" "3796929").PN.	USPAT	2002/08/06 11:51
-	3	("3386865" "3544858" "3649386").PN.	USPAT	2002/08/06 13:09
-	15	5236861.URPN.	USPAT	2002/08/06 12:30
-	8	("4539744" "5106777" "5236861" "5256593" "5273928" "5330928" "5453395" "5472902").PN.	USPAT	2002/08/06 12:32
-	14	("3873371" "4013484" "4023195" "4027380" "4178191" "4253229" "4417385" "4466178" "4554726" "4698899" "5045898" "5100810" "5173438" "5240874").PN.	USPAT	2002/08/06 12:44
-	5	("4980311" "5112772" "5116779" "5369051" "5455438").PN.	USPAT	2002/08/06 12:58
-	2	("5418176" "5422300").PN.	USPAT	2002/08/06 13:04
-	3	5946577.URPN.	USPAT	2002/08/06 13:04
-	7498	(gate) WITH (locos or "field oxide")	USPAT; US-PGPUB	2002/08/06 13:10
-	6987	((gate) WITH (locos or "field oxide")) and (MOSFET or MOS or FET or transistor)	USPAT; US-PGPUB	2002/08/06 13:11
-	124	("semi recessed" or semirecessed) SAME locos	USPAT; US-PGPUB	2002/08/06 13:11
-	5702	((gate) WITH (locos or "field oxide")) and (MOSFET or MOS or FET or transistor) and (ion or implant)	USPAT; US-PGPUB	2002/08/06 13:15
-	2815	((gate) WITH (locos or "field oxide")) and (MOSFET or MOS or FET or transistor) and ((ion or implant) SAME (thermal or oxidation or oxidizing))	USPAT; US-PGPUB	2002/08/06 13:18
-	308	((((gate) WITH (locos or "field oxide")) and (MOSFET or MOS or FET or transistor)) and ((ion or implant) SAME (thermal or oxidation or oxidizing))) and offset	USPAT; US-PGPUB	2002/08/06 13:19
-	60	438/447.ccls.	USPAT; US-PGPUB	2002/08/06 13:38
-	5	("4965221" "5137843" "5173444" "5246537" "5374584").PN.	USPAT	2002/08/06 13:32
-	168	438/525.ccls.	USPAT; US-PGPUB	2002/08/06 13:47
-	694	438/301.ccls.	USPAT; US-PGPUB	2002/08/06 13:57
-	293	438/299.ccls.	USPAT; US-PGPUB	2002/08/06 13:49
-	66	438/299.ccls. and locos	USPAT; US-PGPUB	2002/08/06 13:50
-	40	locos and offset	EPO; JPO	2002/08/06 13:50
-	629	438/301.ccls. not 438/299.ccls.	USPAT; US-PGPUB	2002/08/06 13:57
-	616	(438/301.ccls. not 438/299.ccls.) not 438/298.ccls.	USPAT; US-PGPUB	2002/08/06 13:59
-	614	((438/301.ccls. not 438/299.ccls.) not 438/298.ccls.) not 438/525.ccls.	USPAT; US-PGPUB	2002/08/06 13:58
-	105	((438/301.ccls. not 438/299.ccls.) not 438/298.ccls.) not 438/525.ccls.) and locos	USPAT; US-PGPUB	2002/08/06 13:59
-	1548	(selective or selectively) WITH (oxide or oxidation) with (source or drain or "source/drain")	USPAT; US-PGPUB	2002/08/06 16:09

-	1293	((selective or selectively) WITH (oxide or oxidation) with (source or drain or "source/drain")) and (MOSFET or MOS or FET or transistor)	USPAT; US-PPGPUB	2002/08/06 16:09
-	396	((selective or selectively) WITH (oxide or oxidation) with (source or drain or "source/drain")) and (MOSFET or MOS or FET or transistor)) and (locos or recessed)	USPAT; US-PPGPUB	2002/08/06 16:10